

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Rating	Unit
V_{DSS}	Drain-Source Voltage		-20	V
V_{GSS}	Gate-Source Voltage		± 12	
I_D^*	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-4.6	A
		$T_A = 70^\circ\text{C}$	-3.7	
I_{DM}^*	300 μs Pulsed Drain Current	$T_A = 25^\circ\text{C}$	-18.6	
		$T_A = 70^\circ\text{C}$	-14.9	
I_S^*	Diode Continuous Forward Current		-1	$^\circ\text{C}$
T_J	Maximum Junction Temperature		150	
T_{STG}	Storage Temperature Range		-55 to 150	
P_D^*	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	1.56	W
		$T_A = 70^\circ\text{C}$	1.0	
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient	$t \leq 10\text{s}$	80	$^\circ\text{C/W}$
		Steady state	120	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	Steady state	52	

Note : *Surface Mounted on 1in² pad area, $t \leq 10\text{sec}$.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_{DS}=-250\mu\text{A}$	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{V}$, $V_{GS}=0\text{V}$	-	-	-1	μA
		$T_J=85^\circ\text{C}$	-	-	-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_{DS}=-250\mu\text{A}$	-0.5	-0.7	-1	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 12\text{V}$, $V_{DS}=0\text{V}$	-	-	± 100	nA
$R_{DS(ON)}^a$	Drain-Source On-State Resistance	$V_{GS}=-4.5\text{V}$, $I_{DS}=-4.6\text{A}$	-	38	48	m Ω
		$V_{GS}=-2.5\text{V}$, $I_{DS}=-2.9\text{A}$	-	52	70	
		$V_{GS}=-1.8\text{V}$, $I_{DS}=-1.5\text{A}$	-	76	110	
V_{SD}^a	Diode Forward Voltage	$I_{SD}=-1\text{A}$, $V_{GS}=0\text{V}$	-	-0.7	-1	V
Gate Charge Characteristics^b						
Q_g	Total Gate Charge	$V_{DS}=-10\text{V}$, $V_{GS}=-4.5\text{V}$, $I_{DS}=-4.6\text{A}$	-	6.8	-	nC
Q_{gs}	Gate-Source Charge		-	0.8	-	
Q_{gd}	Gate-Drain Charge		-	2.5	-	

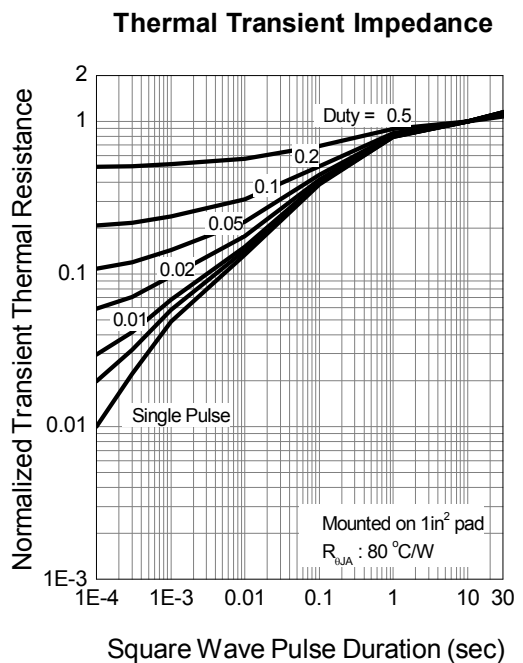
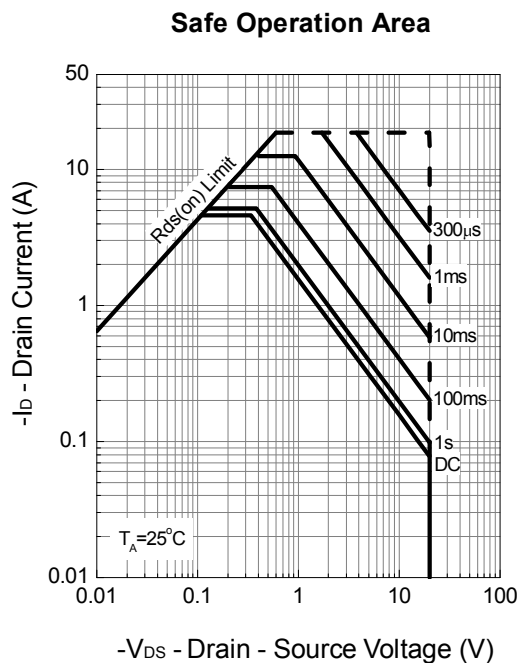
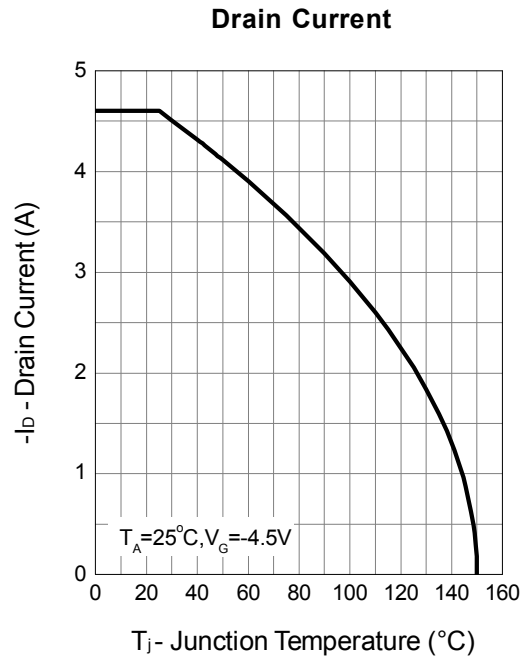
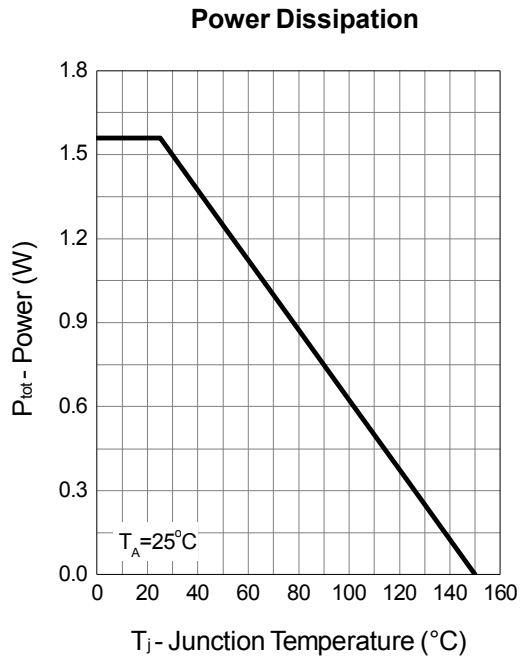
Electrical Characteristics (Cont.) ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Dynamic Characteristics^b						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	-	3.6	-	Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-10V,$ Frequency=1.0MHz	-	590	-	pF
C_{oss}	Output Capacitance		-	122	-	
C_{rss}	Reverse Transfer Capacitance		-	92	-	
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-10V, R_L=10\Omega,$ $I_{DS}=-1A, V_{GEN}=-4.5V,$ $R_G=6\Omega$	-	7.2	-	ns
t_r	Turn-on Rise Time		-	13.4	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	26	-	
t_f	Turn-off Fall Time		-	17	-	
t_{rr}	Reverse Recovery Time	$I_{SD}=-4.6A, di_{SD}/dt = 100A/\mu s$	-	18	-	ns
Q_{rr}	Reverse Recovery Charge		-	7	-	nC

Note a : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

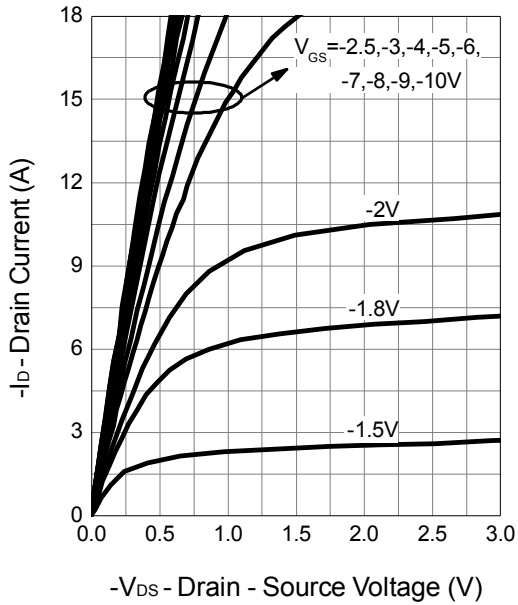
Note b : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

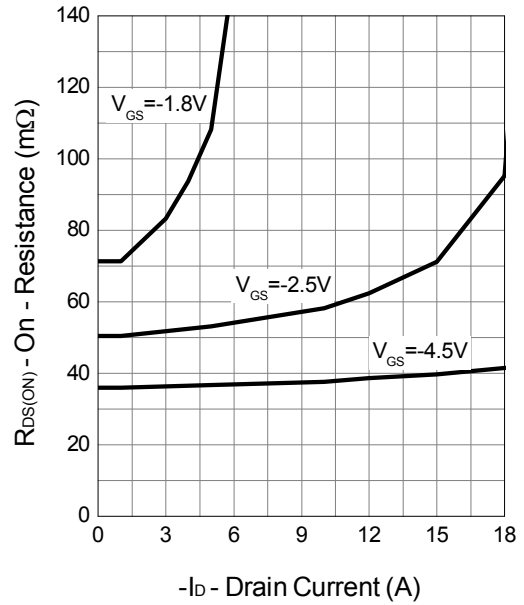


Typical Operating Characteristics (Cont.)

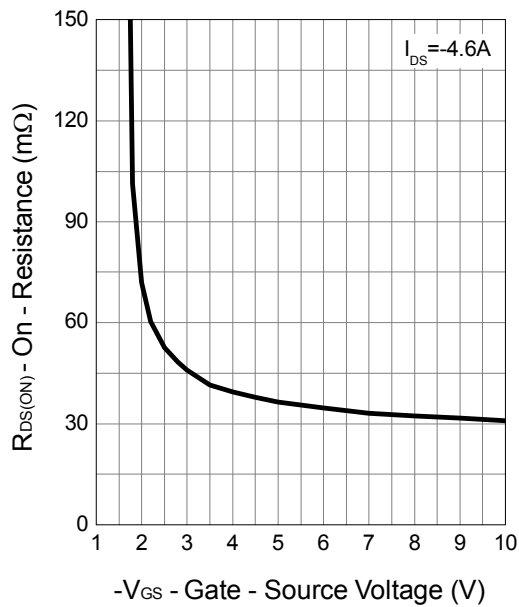
Output Characteristics



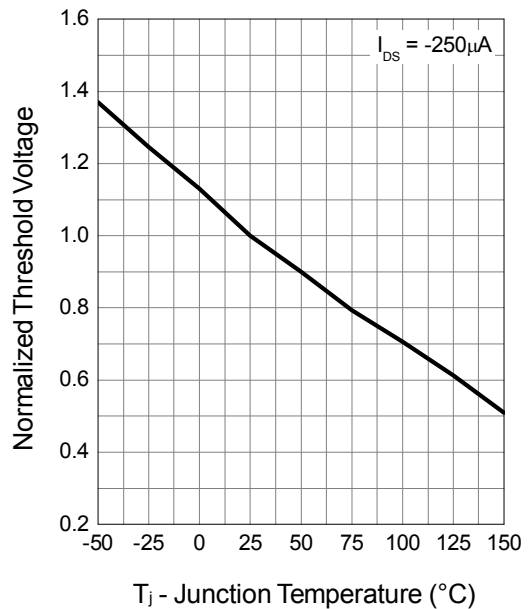
Drain-Source On Resistance



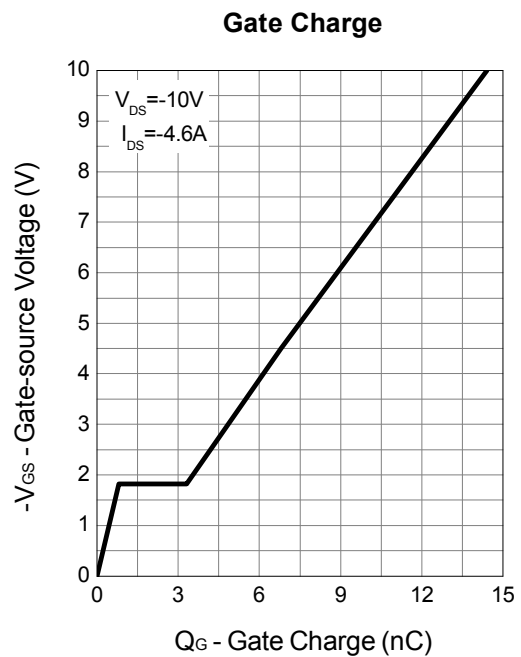
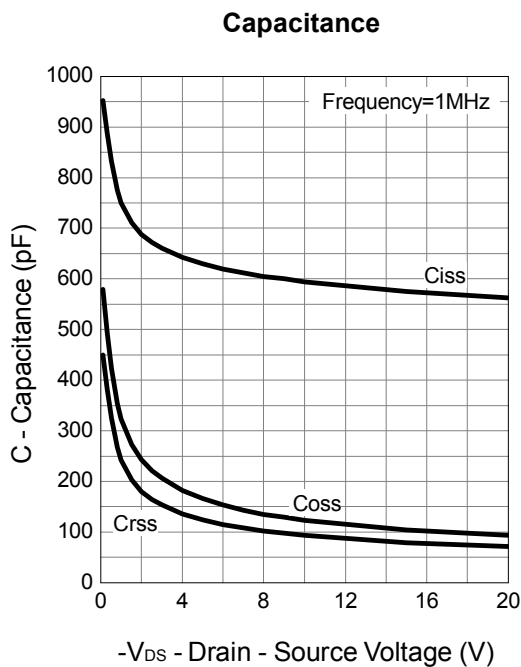
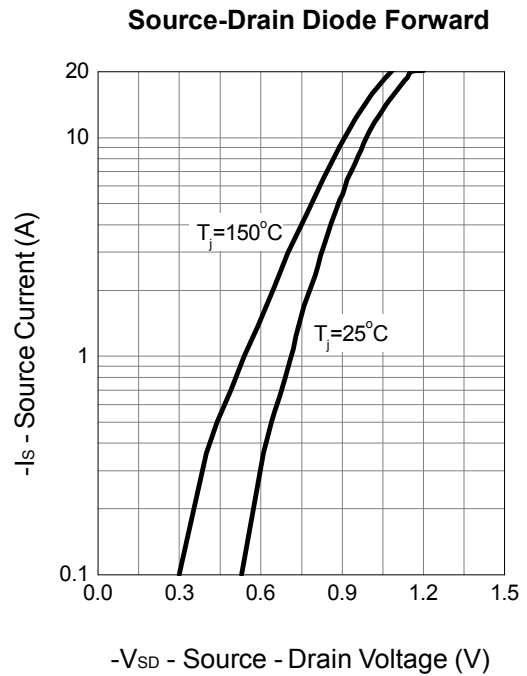
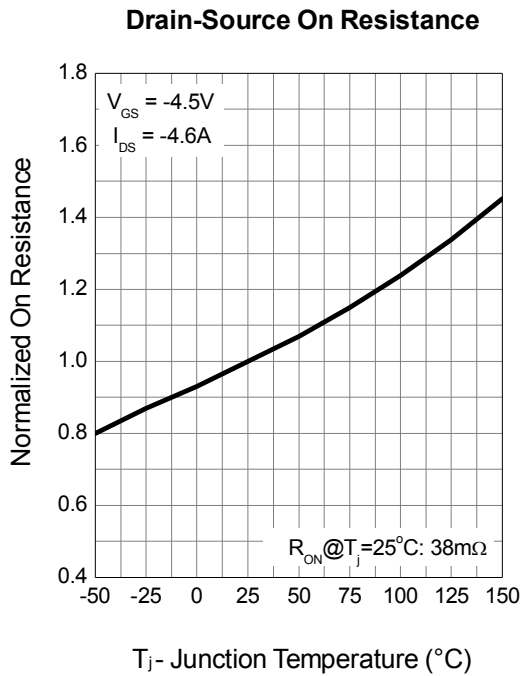
Gate-Source On Resistance



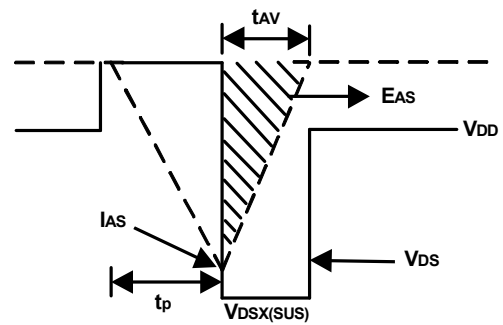
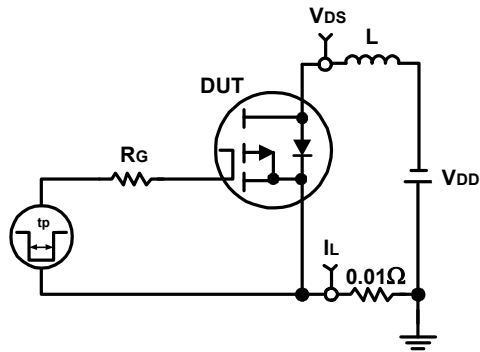
Gate Threshold Voltage



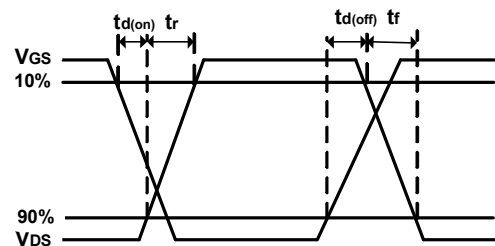
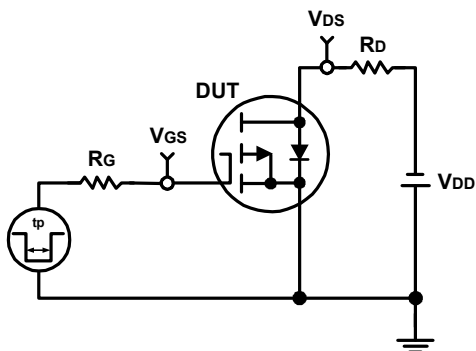
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms

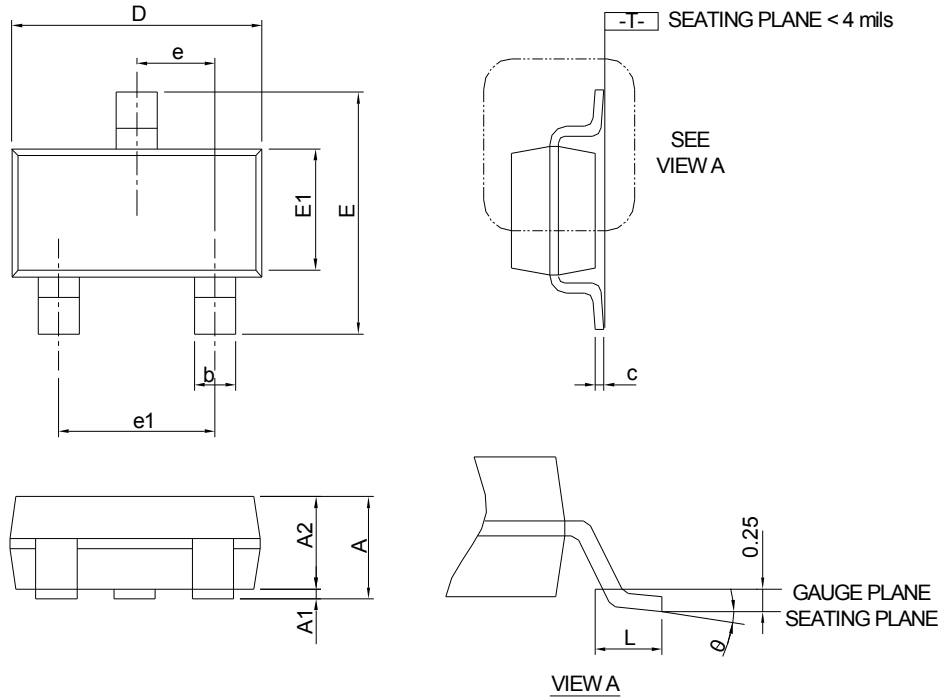


Switching Time Test Circuit and Waveforms



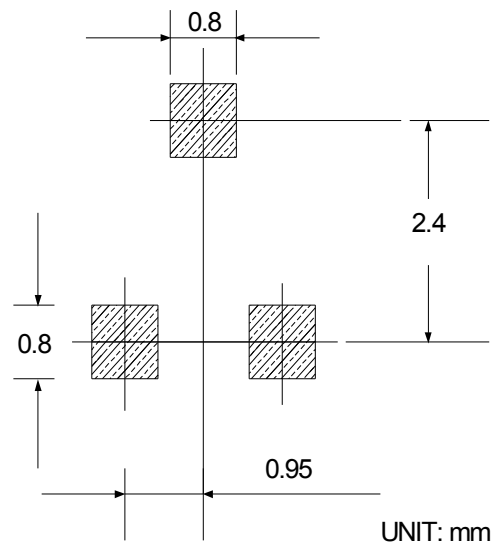
Package Information

SOT-23-3



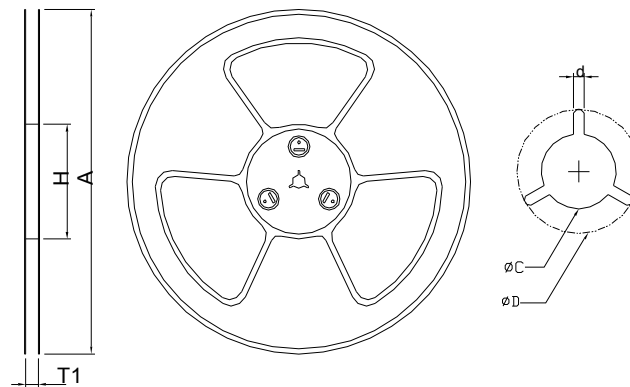
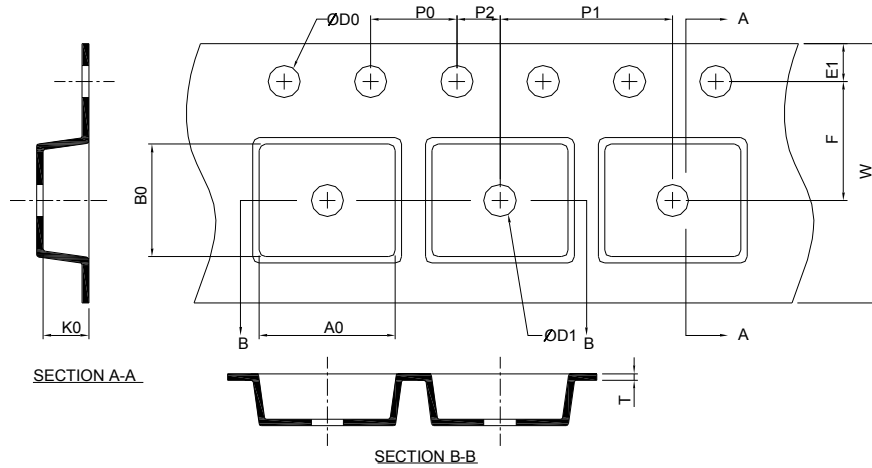
SYMBOL	SOT-23-3			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.20	-	0.047
A1	0.00	0.08	0.000	0.003
A2	0.90	1.12	0.035	0.044
b	0.30	0.50	0.012	0.020
c	0.08	0.22	0.003	0.009
D	2.70	3.10	0.106	0.122
E	2.60	3.00	0.102	0.118
E1	1.40	1.80	0.055	0.071
e	0.95 BSC		0.037 BSC	
e1	1.90 BSC		0.075 BSC	
L	0.30	0.60	0.012	0.024
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



Note : Dimension D and E1 do not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 10 mil per side.

Carrier Tape & Reel Dimensions

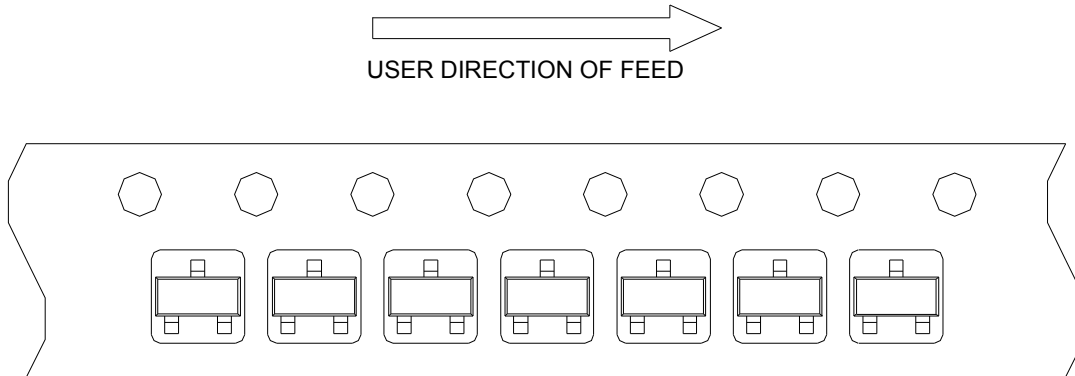


Application	A	H	T1	C	d	D	W	E1	F
SOT-23-3	178.0±2.00	50 MIN.	8.4+2.00 -0.00	13.0+0.50 -0.20	1.5 MIN.	20.2 MIN.	8.0±0.30	1.75±0.10	3.5±0.05
	P0	P1	P2	D0	D1	T	A0	B0	K0
	4.0±0.10	4.0±0.10	2.0±0.05	1.5+0.10 -0.00	1.0 MIN.	0.6+0.00 -0.40	3.20±0.20	3.10±0.20	1.50±0.20

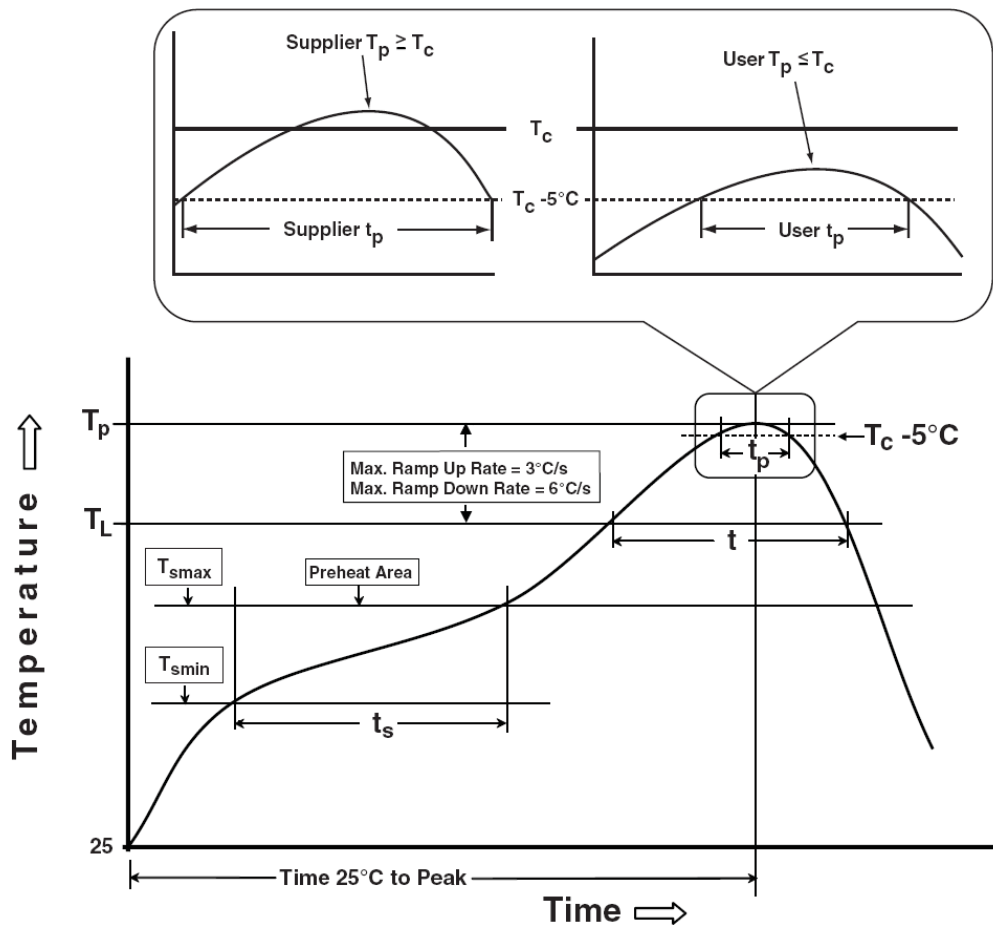
(mm)

Taping Direction Information

SOT-23-3



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
* Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		

Table 1. SnPb Eutectic Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (T_c)

Package Thickness	Volume mm ³ <350	Volume mm ³ 350-2000	Volume mm ³ >2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm	250 °C	245 °C	245 °C

Reliability Test Program

Test item	Method	Description
SOLDERABILITY	JESD-22, B102	5 Sec, 245°C
HTRB	JESD-22, A108	1000 Hrs, 80% of VDS max @ T_{jmax}
HTGB	JESD-22, A108	1000 Hrs, 100% of VGS max @ T_{jmax}
PCT	JESD-22, A102	168 Hrs, 100%RH, 2atm, 121°C
TCT	JESD-22, A104	500 Cycles, -65°C~150°C

Customer Service

Sinopower Semiconductor, Inc.

5F, No. 6, Dusing 1St Rd., Hsinchu Science Park,

Hsinchu, 30078, Taiwan

TEL: 886-3-5635818 Fax: 886-3-5642050